



Product Overview

HGT1S10N120BNS: IGBT, 1200V, NPT

For complete documentation, see the data sheet.

HGT1S10N120BNST is based on Non- Punch Through(NPT) IGBT designs. The IGBT is ideal for many high voltage switching applications operating at moderate frequencies where low conduction losses are essential, such as UPS, solar inverter, motor control and power supplies.

Features

- 17A, 1200V, TC = 110°C
- Low Saturation Voltage : $V_{CE(sat)} = 2.45\text{ V @ } I_C = 10\text{A}$
- Typical Fall Time.140ns at $T_J = 150^\circ\text{C}$
- Short Circuit Rating
- Low Conduction Loss

Applications

- Uninterruptible Power Supply

Part Electrical Specifications																
Product	Compliance	Status	$V_{ES}^{(BR)C}$ Typ (V)	I_C Max (A)	$V_{CE(sat)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_{rr} Typ (A)	Gate Charge Typ (nC)	Short Circuit Withs tand (μs)	E_{AS} Typ (mJ)	P_D Max (W)	Co- Pack aged Diode	Pack age Type
HGT1S10N120BNST	Pb-free	Active	1200	17	2.45	-	0.8	0.32	-	-	100	8	80	298	No	D2PA K-3 / TO- 263-2

For more information please contact your local sales support at www.onsemi.com.

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